

## Silicon NPN Power Transistors

2SD1763

## DESCRIPTION

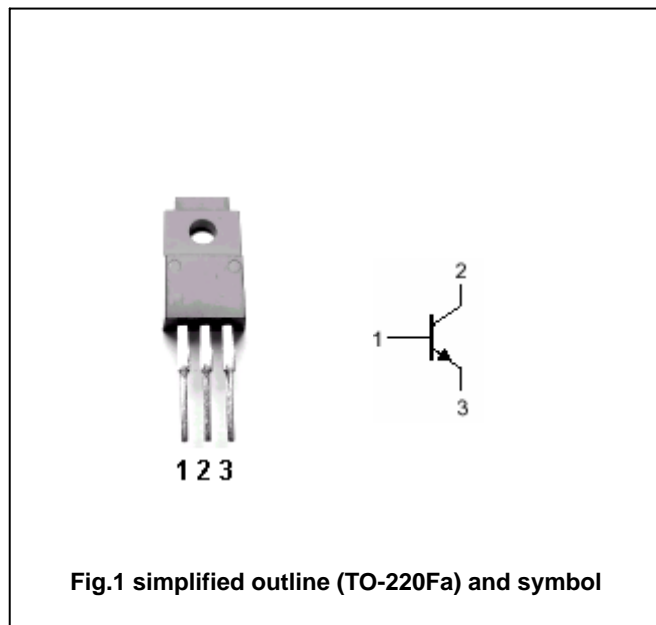
- With TO-220Fa package
- High breakdown voltage  $V_{CEO}$
- Complement to type 2SB1186
- High transition frequency

## APPLICATIONS

- For low frequency power amplifier applications

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	120	V
$V_{CEO}$	Collector-emitter voltage	Open base	120	V
$V_{EBO}$	Emitter-base voltage	Open collector	5	V
$I_C$	Collector current (DC)		2	A
$I_{CM}$	Collector current-Peak		3	A
$P_C$	Collector power dissipation	$T_C=25$	20	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

## Silicon NPN Power Transistors

2SD1763

## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =1mA, I <sub>B</sub> =0	120			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =50 μA, I <sub>E</sub> =0	120			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =50 μA, I <sub>C</sub> =0	5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =1A; I <sub>B</sub> =0.1A			0.4	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =1A; I <sub>B</sub> =0.1A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =100V, I <sub>E</sub> =0			1	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =4V; I <sub>C</sub> =0			1	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =0.1A; V <sub>CE</sub> =5V	100		320	
f <sub>T</sub>	Transition frequency	I <sub>E</sub> =-0.1A; V <sub>CE</sub> =5V		80		MHz
C <sub>ob</sub>	Output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =10V, f=1MHz		20		pF

◆ h<sub>FE</sub> Classifications

E	F
100-200	160-320

PACKAGE OUTLINE

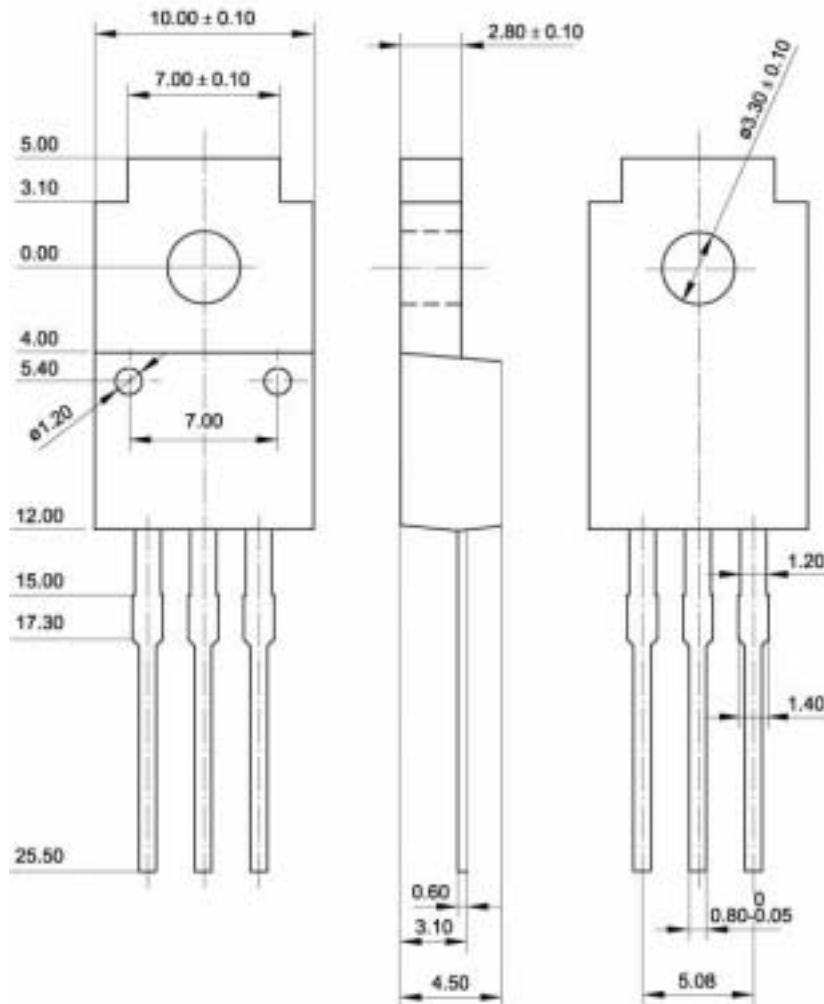


Fig.2 Outline dimensions (unindicated tolerance:  $\pm 0.15$  mm)